

Amendments to the Specification:

Please amend the specification as follows:

Page 1, before the 1st paragraph insert the following:

OK
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8/22/05

This application is a continuation of application Serial No. 10/359,190, filed February 6, 2003, ^{now US 6,654,314} which is in turn a divisional of application Serial No. 10/093,935, filed on March 11, 2002, ^{now US pat. 6,535,456} which is in turn a continuation of application Serial No. 09/916,578, filed on July 30, 2001, now U.S. Patent No. 6,373,785, which is in turn a continuation of application Serial No. 09/812,820, filed on March 21, 2001, now U.S. Patent No. 6,317,382, which is in turn a divisional of application Serial No. 09/433,338, filed November 4, 1999, now U.S. Patent No. 6,249,481, which in turn is a divisional of application Serial No. 09/236,832, filed January 25, 1999, now U.S. Patent No. 5,995,442, which is in turn a divisional of application Serial No. 09/017,948, filed February 3, 1998, now U.S. Patent No. 5,926,436, which is in turn a continuation of application Serial No. 08/779,902, filed January 7, 1997, now U.S. Patent No. 5,740,122, which is in turn a continuation of application Serial No. 08/463,394, filed June 5, 1995, now U.S. Patent No. 5,612,925, which is a continuation of application Serial No. 08/223,222, filed April 5, 1994, now U.S. Patent No. 5,500,829, which is in turn a divisional of application Serial No. 07/775,602, filed October 15, 1991, now U.S. Patent No. 5,313,437, which claims priority from Japanese Patent Application 2-273170, filed October 15, 1990 and Japanese Patent Application 3-255354, filed October 2, 1991. The entire contents of each of the aforementioned applications are incorporated by reference herein.

Please replace paragraph starting at page 3, line 9 through page 6, line 25 with the following rewritten paragraph:

SUMMARY OF THE INVENTION

~~An object of the present invention is to provide, with due consideration to the drawbacks of such conventional devices, a semiconductor memory device provided with an easily controllable dynamic memory which can be accessed at high speed.~~